

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0$	—	—	± 100	nA
Drain Cut-off Current		I_{DSS}	$V_{DS} = -60V, V_{GS} = 0$	—	—	-10	μA
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-60	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = -10V, I_D = -1mA$	-2	—	-3.5	V
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = -10V, I_D = -50mA$	100	—	—	mS
Drain-Source ON Resistance		$R_{DS(ON)}$	$I_D = -50mA, V_{GS} = -10V$	—	1.3	2.0	Ω
Drain-Source ON Voltage		$V_{DS(ON)}$	$I_D = -50mA, V_{GS} = -10V$	—	-65	-100	mV
Input Capacitance		C_{iss}	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$	—	73	85	pF
Reverse Transfer Capacitance		C_{rss}	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$	—	15	22	pF
Output Capacitance		C_{oss}	$V_{DS} = -10V, V_{GS} = 0, f = 1MHz$	—	48	60	pF
Switching Time	Rise Time	t_r	<p>$I_D = -100mA$ $V_{IN} : t_r, t_f < 5ns$ D.U. $\leq 1\%$ ($Z_{out} = 50\Omega$)</p>	—	8	—	ns
	Turn-on Time	t_{on}		—	14	—	
	Fall Time	t_f		—	35	—	
	Turn-off Time	t_{off}		—	100	—	



